

App. Serial No. 10/538,217  
Docket No.: NL021418 US

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**APR 30 2007**

**In the Specification:**

Please amend the paragraph at page 5, lines 29-31 as follows:

This process provides a ready means of manufacturing a trench MOSFET with a thick oxide plug at the bottom of the trench to reduce capacitance between the gate 10 and the drain ~~2~~ 4.